

What is claimed is

- 1 1. A laser CVD device comprising:
 - 2 a plasma unit for turning pretreating gas into a plasma state in atmosphere and
 - 3 supplying a plasma gas to a substrate;
 - 4 means for radiating a laser beam to a deposition area on the substrate;
 - 5 means for supplying film forming gas to the deposition area; and
 - 6 means for sealing the film forming gas isolated from an external atmosphere,
 - 7 wherein
 - 8 the deposition area of said substrate is pretreated by said plasma unit and a film
 - 9 is formed over said deposition area of said substrate by activating the film forming gas
 - 10 by said laser beam.
- 1 2. A laser CVD device as claimed in claim 1, wherein said plasma unit makes
- 2 the plasma state by arc discharge.
- 1 3. A laser CVD device as claimed in claim 1, further comprising a X-Y table on
- 2 which said substrate is posited.
- 1 4. A laser CVD device as claimed in claim 2, wherein said plasma unit includes
- 2 a plasma generating chamber 21, a gas inlet for receiving pretreating gas to the plasma
- 3 generating chamber, and a electrode for causing the pretreating gas to generate arc
- 4 discharge.
- 1 5. A laser CVD device as claimed in claim 4, wherein said plasma unit further
- 2 includes a metal net for preventing the arc discharge from being effected on the
- 3 substrate 10.
- 1 6. A laser CVD device correcting apparatus as claimed in claim 1, wherein said

2 pretreating gas is one of air, nitrogen and argon.

1 7. A laser CVD method comprising steps of: ✓

2 turning pretreating gas into a plasma state by arc discharge;

3 supplying said pretreating gas in the plasma state to bring it into contact with a
4 film formation face of a substrate;

5 supplying film forming gas to the film formation face of the substrate isolated
6 from the external atmosphere;

7 irradiating the film formation face of said substrate with a laser beam to
8 activate said film forming gas; and

9 causing said activated film forming gas to form a film over said film formation
10 face of the substrate.

1 8. A pattern defect correcting apparatus comprising: ~

2 a substrate holder capable of moving a substrate having a pattern, said pattern
3 having a defective portion;

4 pretreating unit for turning pretreating gas into a plasma state by arc discharge
5 and for supplying plasma state gas to the substrate on said substrate holder,;

6 film forming unit which is provided with means for radiating a laser beam and
7 means for sealing film forming gas isolated from an external atmosphere; and

8 control unit, wherein

9 said control unit controls said pretreating unit to supply said the plasma state
10 gas to the defective portion on said substrate,

11 said control unit controls said film forming unit to isolate said film forming gas
12 from an external atmosphere and to supply said film forming gas onto the defective
13 portion on said substrate, and

14 said control unit controls said film forming unit to irradiate the defective
15 portion on said substrate with said laser beam to activate said film forming, thereby

16 causing film formation at the defective portion on said substrate.

1 9. A pattern defect correcting method for correcting a defective portion on a substrate,
2 said method comprising the steps of:
3 turning pretreating gas into a plasma state by arc discharge,
4 supplying said pretreating gas in the plasma state the defective portion of said
5 substrate,
6 sealing film forming gas to a film formation face corresponding to the
7 defective portion of said substrate while being isolated from an external atmosphere,
8 irradiating said film formation face with a laser beam to activate said film
9 forming gas, and
10 forming a film over the defective portion of said substrate to correct the
11 defective portion.